

A¹
variation of power spectrum density of 2.0 or less for undulation components at a wavelength of from 3 mm to 20 mm of the wafer back surface.

Please add the following new claims:

--15. The method for producing a semiconductor wafer according to claim 14, which utilizes a semiconductor wafer having wafer warpage of 20 μ m or less.

A²
--16. The method for producing a semiconductor wafer according to claim 14, which utilizes a silicon semiconductor wafer.

--17. The method for producing a semiconductor wafer according to claim 15, which utilizes a silicon semiconductor wafer.--